

Philips

Diode BAQ806

Datasheet

AM PIN Diode

BAQ806

100V

DATASHEET

OEM – Philips

Source: Philips Databook 1999

AM PIN diode**about BAQ806****FEATURES**

- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- UL 94V-0 classified plastic package
- Shipped in 12 mm embossed tape.

DESCRIPTION

DO-214AC surface mountable package with glass passivated chip.

The well-defined void-free case is of a transfer-moulded thermo-setting plastic.

APPLICATIONS

- RF attenuator with low distortion for frequencies above 100 kHz.

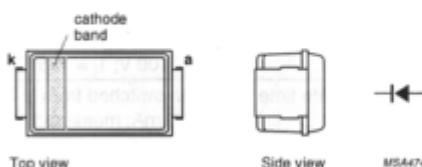


Fig.1 Simplified outline (SOD106) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage	–	100	V
V_R	continuous reverse voltage	–	100	V
T_{stg}	storage temperature	–65	+175	°C
T_j	junction temperature	–65	+150	°C

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ELECTRICAL CHARACTERISTICS

 $T_j = 25^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	forward voltage	$I_F = 100 \text{ mA}$; see Figs 2 and 3	—	0.9	1.1	V
		$I_F = 100 \text{ mA}; T_j = T_{j,\text{max}}$; see Figs 2 and 3	—	0.7	0.9	V
I_R	reverse current	$V_R = 100 \text{ V}$; see Fig. 4	—	—	0.1	μA
		$V_R = 100 \text{ V}; T_j = 125^\circ\text{C}$; see Fig. 4	—	—	30	μA
τ	charge carrier life time	when switched from $I_F = 10 \text{ mA}$ to $I_R = 6 \text{ mA}$; measured at 10% of I_R ; see Fig. 13	15	25	—	μs
C_d	diode capacitance	$f = 1 \text{ MHz}$; see Figs 5, 6, 7 and 8	—	9	11	pF
		$V_R = 0 \text{ V}$	—	5	6	pF
		$V_R = 2 \text{ V}$	—	—	—	pF
r_D	diode forward resistance	$f = 100 \text{ kHz}$; see Figs 9 and 14	—	—	—	—
		$I_F = 10 \mu\text{A}$	—	3300	6000	Ω
		$I_F = 100 \mu\text{A}$	—	560	900	Ω
		$I_F = 1 \text{ mA}$	—	62	90	Ω
		$I_F = 10 \text{ mA}$	—	7	10	Ω
r_s	diode series resistance	$f = 100 \text{ kHz}$; see Figs 10, 11 and 12	—	—	—	—
		$V_R = 0 \text{ V}$	1000	2100	—	$\text{k}\Omega$
		$V_R = 2 \text{ V}$	5000	12000	—	$\text{k}\Omega$
		$f = 1 \text{ MHz}$; see Figs 10, 11 and 12	—	—	—	—
		$V_R = 0 \text{ V}$	25	50	—	$\text{k}\Omega$
		$V_R = 2 \text{ V}$	100	250	—	$\text{k}\Omega$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th,j-tp}$	thermal resistance from junction to tie-point	—	25	K/W
$R_{th,j-a}$	thermal resistance from junction to ambient	note 1	100	K/W
		note 2	150	K/W

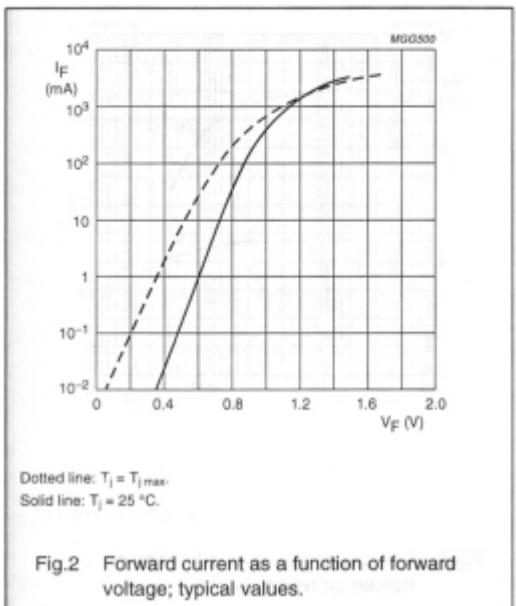
Note

1. Device mounted on Al_2O_3 printed-circuit board, 0.7 mm thick; thickness of copper $\geq 35 \mu\text{m}$, see Fig. 15
2. Device mounted on epoxy-glass printed-circuit board, 1.5 mm thick; thickness of copper $\geq 40 \mu\text{m}$, see Fig. 15.
For more information please refer to the 'General Part of Handbook SC10'

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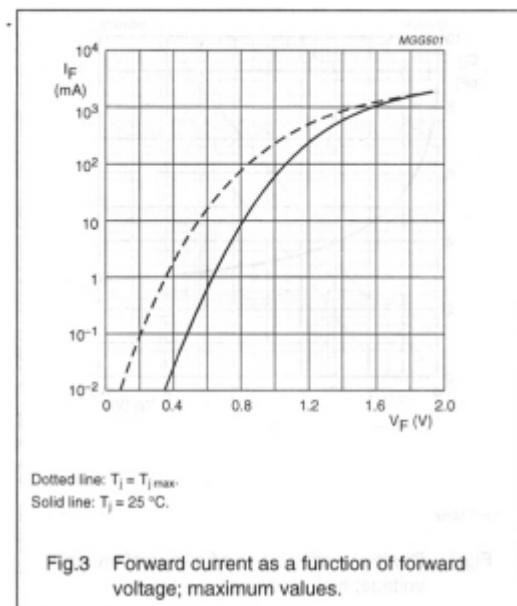
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GRAPHICAL DATA



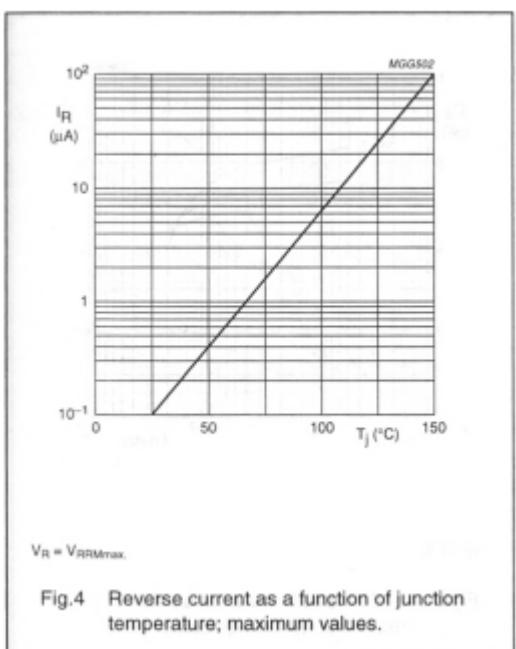
Dotted line: $T_j = T_{j,\max}$.
Solid line: $T_j = 25^\circ\text{C}$.

Fig.2 Forward current as a function of forward voltage; typical values.



Dotted line: $T_j = T_{j,\max}$.
Solid line: $T_j = 25^\circ\text{C}$.

Fig.3 Forward current as a function of forward voltage; maximum values.



$V_R = V_{RRM,\max}$.

Fig.4 Reverse current as a function of junction temperature; maximum values.

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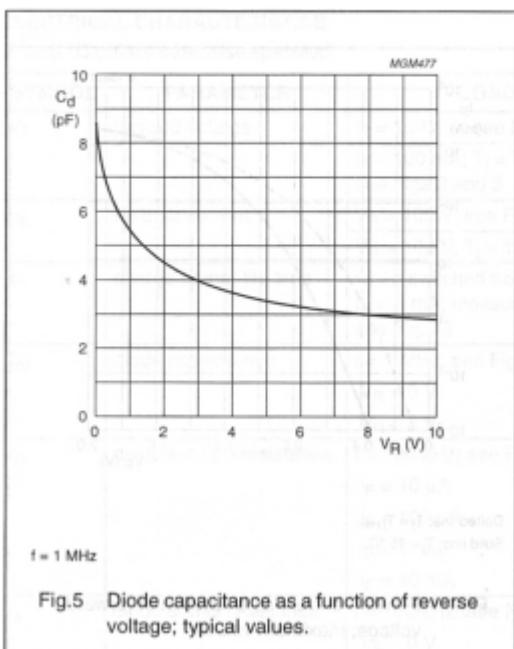


Fig.5 Diode capacitance as a function of reverse voltage; typical values.

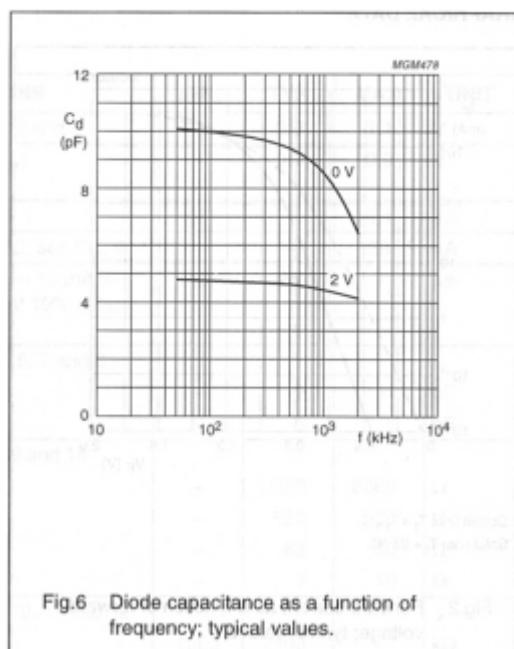


Fig.6 Diode capacitance as a function of frequency; typical values.

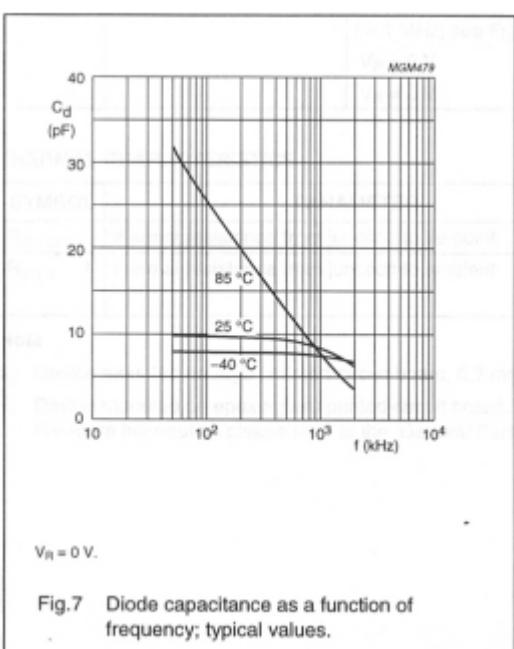


Fig.7 Diode capacitance as a function of frequency; typical values.

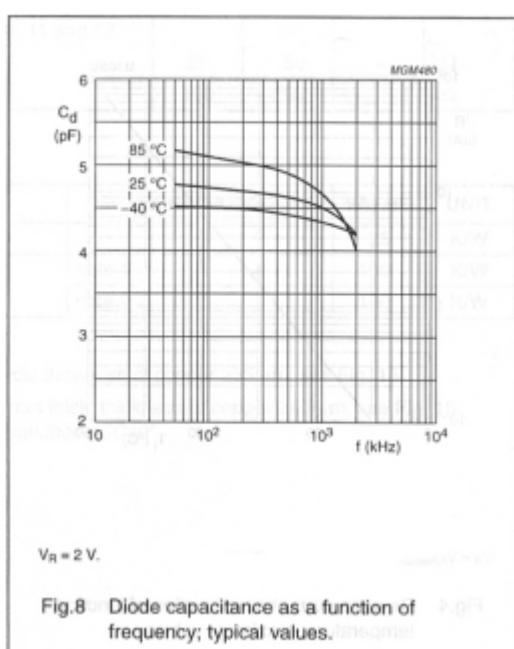
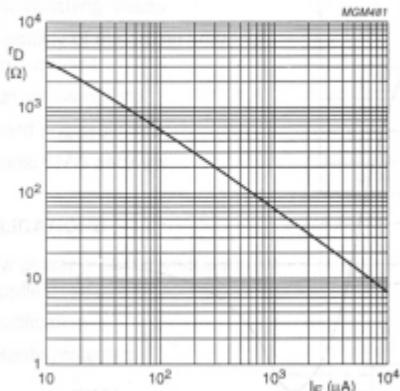


Fig.8 Diode capacitance as a function of frequency; typical values.

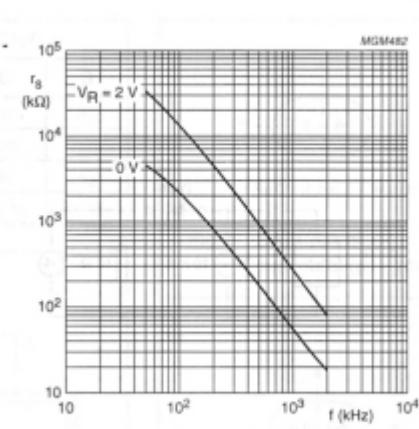
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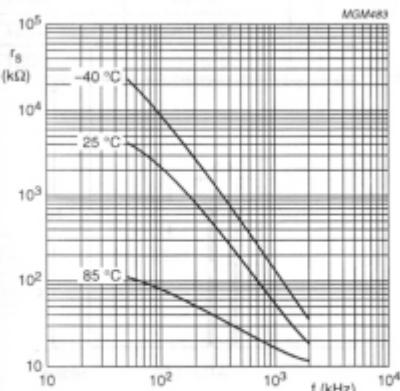
$f = 100 \text{ kHz}$; see Fig. 14.

Fig.9 Diode forward resistance as a function of forward current; typical values.



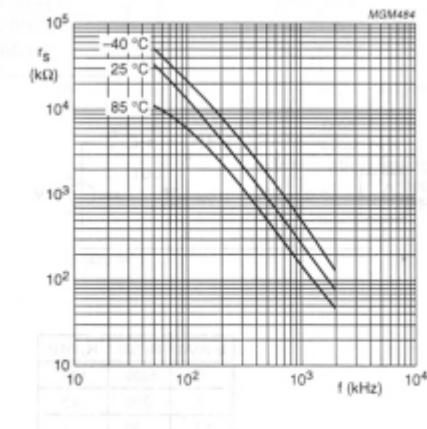
$T_j = 25^\circ\text{C}$.

Fig.10 Diode series resistance as a function of frequency; typical values.



$V_R = 0 \text{ V}$.

Fig.11 Diode series resistance as a function of frequency; typical values.



$V_R = 2 \text{ V}$.

Fig.12 Diode series resistance as a function of frequency; typical values.

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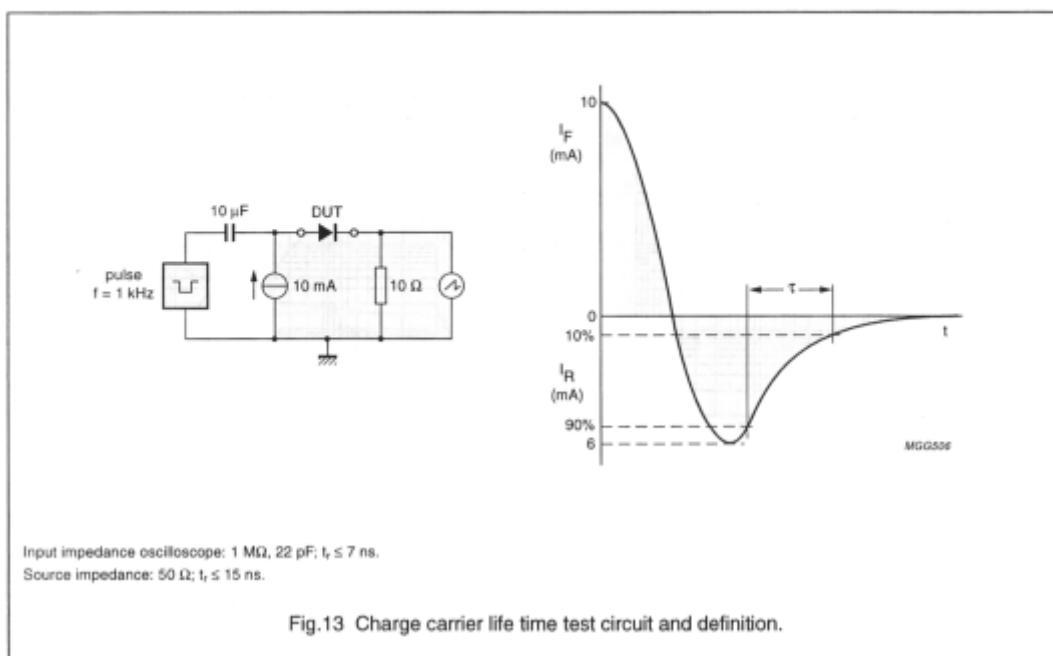


Fig.13 Charge carrier life time test circuit and definition.

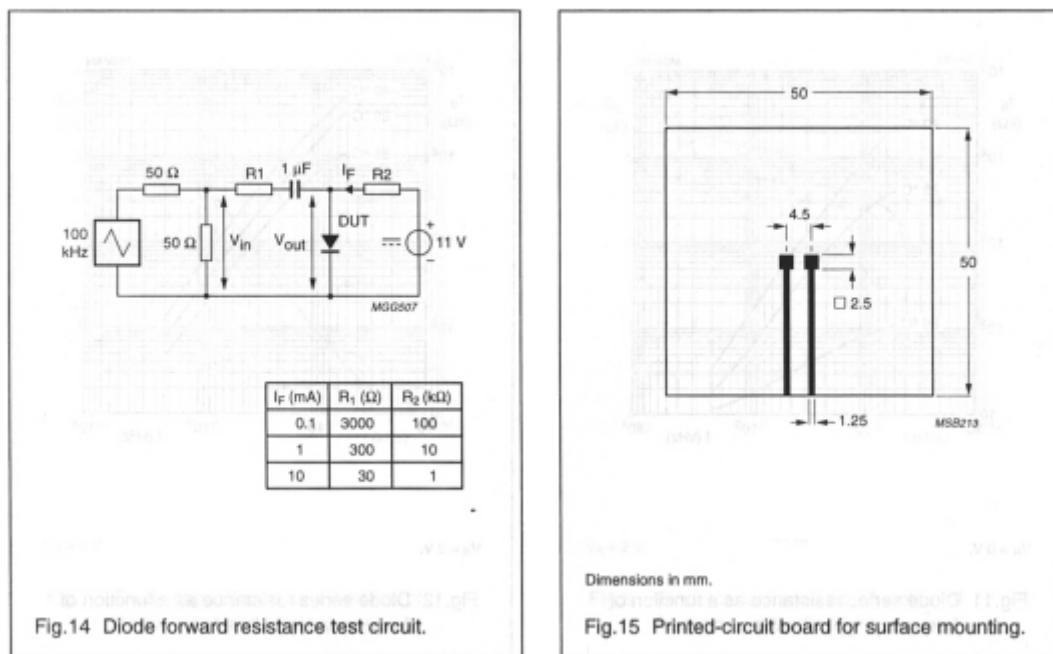
Dimensions in mm.
Pad dimensions are considered to be 0.5×0.5 mm².

Fig.15 Printed-circuit board for surface mounting.